

Topic number: ??

Guideline for abstracts prepared for 32nd International Symposium on Dry Process (DPS2010)

A. Firstauthor¹, B. Secondauthor¹ and C. Thirdauthor²
¹Nagoya University, Furo-cho, Chikusa, Nagoya, Aichi 464-8603 Japan
²Plasma Nanotechnology Co. Ltd., Nagoya, Aichi 464-8603, Japan
Email: dps2010@plasma.engg.nagoya-u.ac.jp

Include in this space a very short summary of the abstract. Use Times New Roman font, 10 pt, simple interline. Justify left and right. The width of the space for title, authors' names, and affiliations is 160 mm, and the width of the space for the short summary is 140 mm.

1 General information

Contributed papers must be in English and should report an original work. The total length, including figures and references, is **two A4 format pages**. Invited speakers should also prepare two A4 format pages summarizing their presentations. The authors are responsible for the content and style of the contribution. No editing or re-typing will be carried out by DPS Organizing Committee. The contributions will be reproduced without reduction or modification. Contributed papers which do not conform to the format described below may be rejected. Each abstract should be submitted via the official web site of DPS2009:

<http://www.plasma.engg.nagoya-u.ac.jp/dps2010>

Contribution submitted by email, fax, and conventional mail cannot be accepted. The submitted file must be a **Portable Document Format (PDF) document**, and an abstract prepared using Microsoft Word or LaTeX should be converted to a PDF file.

The deadline for receipt of two-page abstracts is July 12, 2010. All contributed papers will be refereed by DPS Organizing Committee, and authors will be notified of acceptance or rejection of their abstracts by **the beginning of September, 2010**. Based on scientific quality, DPS Organizing Committee will select about 20 oral presentations. Accepted contributions and invited papers will appear on the DPS2010 Extended Abstract that will be distributed to the participants at the conference site. No publication will occur, unless the registration fee, for at least one of the authors, is received on or before **October 10, 2010**.

2 Detailed information

2.1 Format

The abstract should be typewritten on A4 format papers at two columns. The total length, including figures and references, is two pages for invited and contributed papers. The pages must not be numbered.

Table 1 Types and sizes of fonts which should be used in the abstract of DPS2009.

Place	Type and size
Title	Arial 16, bold
Authors' name	Times 12, normal
Affiliations	Times 10, italic
Short summary	Times 10, normal
Main text	Times 10, normal
Figure and table captions	Arial 9, normal
Major headings	Times 11, bold
Subheadings	Times 10, italic

Margins are 2.5 cm for top, bottom, left, and right (if US letter format is used, set right at 3.1 cm). The distance between the columns is 0.5 cm. Place an indent of 6 mm at the beginning of each paragraph. However, no indents should be placed for the first paragraph after headings. The fonts should be Times New Roman (or similar fonts) except for the title and captions. Table 1 summarizes the fonts which should be used in the abstract. If you use LaTeX with the style file "DPS2010.sty", the fonts are assigned automatically and you do not have to take care of that.

2.2 Figures

Abstracts may include figures. Monochromatic figures are recommended since the Extended Abstract will contain no color-printed pages. A caption should be attached to each figure. An example of figures is shown in Fig. 1.

2.3 Equations

An indent of 10 mm should be placed at the left hand side of equations. Equation numbers must be in parentheses and place flush with right-hand margin of the column. An example of equations is given by

$$\frac{\partial n}{\partial t} + \nabla \cdot \Gamma = 0. \quad (1)$$

2.4 Topic number

The topic number corresponding to your abstract



Fig. 1 An example of figures. The monochromatic version of the logo of DPS 30th Anniversary.

should be specified on the top of the abstract. The topic numbers are:

1. Plasma & Surface Reactions
2. Conductor & Si Etching
3. Dielectric Etching
4. Plasma-induced Damage
5. Plasma Diagnostics
6. Modeling and Simulation
7. Plasma Equipment
8. Monitoring Systems
9. CVD/PVD/ALD
10. Plasma processes for 3D Devices, FPD, LED, LASER, Organic Devices, Bio-Application, Medicine, MEMS, Nanotechnologies, and Environmental Technology
11. Equipment technology for dry processes
12. New Dry Process Concepts
13. Wet Process & Reactions

2.5 References

List and number all references at the end of the paper. When referring to them in the text, type the corresponding reference number between brackets as shown at the end of this sentence [1]. Another example is also listed [2].

- [1] J. W. Coburn and H. F. Winters, *J. Vac. Sci. Technol.* **16**, 391 (1979).
- [2] R. W. B. Pearse and A. G. Gaydon, *The Identification of Molecular Spectra* (John Wiley & Sons, New York, 1976).